



### **IXFX78N50P3 Information**



For Reference Only

Part Number IXFX78N50P3

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 78A PLUS247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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### **Certified Quality**

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## **IXFX78N50P3 Specifications**

Manufacturer Part Number         IXFX78N50P3           Manufacturer         IXYS           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         HiPerFET?, Polar3?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         78A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 4mA           Gate Charge (Qg) (Max) @ Vgs         147nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         9900pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         1130W (Tc)           Rds On (Max) @ Id, Vgs         68 mOhm @ 500mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PLUS247?-3           Package / Case         TO-247-3		
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-247-3  Series  HiPerFET?, Polar3?  FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Prive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  147nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  Pgs(Max)  FET Feature  -  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  68 mOhm @ 500mA, 10V  Operating Temperature  Mounting Type  Supplier Device Package  PLUS247?-3  Package / Case	Manufacturer Part Number	IXFX78N50P3
Package         TO-247-3           Series         HiPerFET?, Polar3?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         78A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 4mA           Gate Charge (Qg) (Max) @ Vgs         147nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         9900pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         1130W (Tc)           Rds On (Max) @ Id, Vgs         68 mOhm @ 500mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PLUS247?-3           Package / Case         TO-247-3	Manufacturer	IXYS
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SeriesHiPerFET?, Polar3?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)500VCurrent - Continuous Drain (Id) @ 25°C78A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 4mAGate Charge (Qg) (Max) @ Vgs147nC @ 10VInput Capacitance (Ciss) (Max) @ Vds9900pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)1130W (Tc)Rds On (Max) @ Id, Vgs68 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 500V  Current - Continuous Drain (Id) @ 25°C 78A (Tc)  Drive Voltage (Max Rds On, Min Rds On) 10V  Vgs(th) (Max) @ Id 5V @ 4mA  Gate Charge (Qg) (Max) @ Vgs 147nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds 9900pF @ 25V  Vgs (Max) ±30V  FET Feature - Power Dissipation (Max) 1130W (Tc)  Rds On (Max) @ Id, Vgs 68 mOhm @ 500mA, 10V  Operating Temperature 55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package PLUS247-3  Package / Case Toology (Max) (Max	Package	TO-247-3
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 78A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sv @ 4mA Gate Charge (Qg) (Max) @ Vgs 147nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 68 mOhm @ 500mA, 10V Operating Temperature - Supplier Device Package PLUS247?-3 Package / Case  MOSFET (Metal Oxide)  500V MOSFET (Metal Oxide)  500V 68 MCF 68 (Metal Oxide)  10V  78A (Tc)	Series	HiPerFET?, Polar3?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  78A (Tc)  78A	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Sty @ 4mA  Gate Charge (Qg) (Max) @ Vgs  147nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  9900pF @ 25V  Vgs (Max)  ### ### ### ### #### ###############	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  5V @ 4mA  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  68 mOhm @ 500mA, 10V  Operating Temperature  Jenush Hole  Supplier Device Package  PLUS247?-3  Package / Case  10V  147nC @ 10V  68 mOhm 6 50V  FET Feature  -55°C ~ 150°C (TJ)  Through Hole  PLUS247?-3  Package / Case	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id       5V @ 4mA         Gate Charge (Qg) (Max) @ Vgs       147nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       9900pF @ 25V         Vgs (Max)       ±30V         FET Feature       -         Power Dissipation (Max)       1130W (Tc)         Rds On (Max) @ Id, Vgs       68 mOhm @ 500mA, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PLUS247?-3         Package / Case       TO-247-3	Current - Continuous Drain (Id) @ 25°C	78A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  9900pF @ 25V  Vgs (Max)  ±30V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  68 mOhm @ 500mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PLUS247?-3  Package / Case  TO-247-3	Drive Voltage (Max Rds On, Min Rds On)	10V
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Vgs (Max)±30VFET Feature-Power Dissipation (Max)1130W (Tc)Rds On (Max) @ Id, Vgs68 mOhm @ 500mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePLUS247?-3Package / CaseTO-247-3	Gate Charge (Qg) (Max) @ Vgs	147nC @ 10V
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  68 mOhm @ 500mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PLUS247?-3  Package / Case  TO-247-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 68 mOhm @ 500mA, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package PLUS247?-3  Package / Case TO-247-3	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PLUS247?-3  Package / Case  TO-247-3	Power Dissipation (Max)	1130W (Tc)
Mounting Type Through Hole Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	68 mOhm @ 500mA, 10V
Supplier Device Package PLUS247?-3 Package / Case TO-247-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	PLUS247?-3
Report errors?	Package / Case	TO-247-3
		Report errors?

#### **IXFX78N50P3** Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# **IXFX78N50P3 Payment Methods**









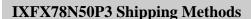
























If you have any question about IXFX78N50P3, please do not hesitate to contact us!

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